

HL6513FM Visible High Power Laser Diode

ODE-208-043 (Z) Rev.0 Oct.20, 2006

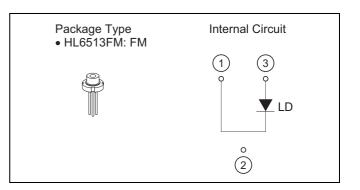
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Description

The HL6513FM is a 0.65 µm band AlGalnP laser diode (LD) with a multi-quantum well (MQW) structure. Its beam divergence (parallel to the junction) has a small variation to the optical output power. It is suitable as light sources for laser scanners and optical equipment for measurement.

Features

- High output power and Wide operating temperature: 70 mW (pulse), PW = 100ns, duty = 50%, $(Topr = 70^{\circ}C)$
- Small package : \$ 5.6 mm
- Visible light output $: \lambda p = 658 \text{ nm Typ}$
- The beam divergence (parallel to the junction) has a small variation to the output power.
- Single longitudinal mode



Absolute Maximum Ratings

			$(T_{\rm C} = 25^{\circ}{\rm C})$
Item	Symbol	Ratings	Unit
Optical output power	Po	50	mW
Pulse optical output power	P _{O(pulse)}	70 * ¹	mW
Laser diode reverse voltage	V _{R(LD)}	2	V
Operating temperature	Topr	-10 to +70 * ²	°C
Storage temperature	Tstg	-40 to +85	°C

Notes: 1. Pulse condition : Pulse width = 100 ns, duty = 50%

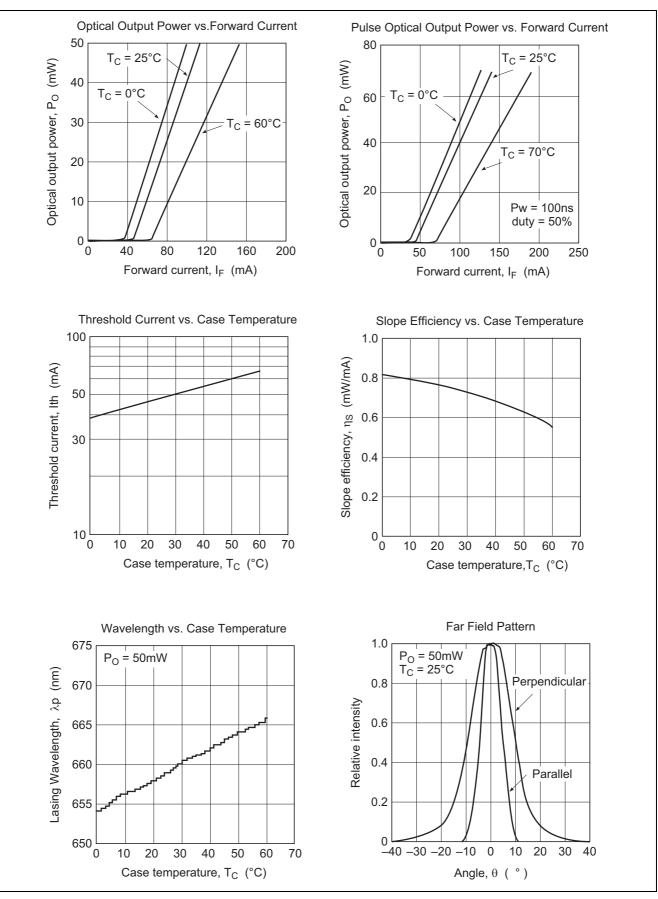
2. The value of -10 to +70°C is effective under pulse operation. The value under CW operation is -10 to +60°C.

Optical and Electrical Characteristics

						$(T_{\rm C} = 25^{\circ}{\rm C})$
ltem	Symbol	Min	Тур	Max	Unit	Test Conditions
Threshold current	lth	30	45	60	mA	—
Operating current	lop	—	115	135	mA	P ₀ = 50 mW
Operating voltage	V _{OP}	2.1	2.6	3.0	V	P ₀ = 50 mW
Beam divergence parallel to the junction	θ//	7	8.5	11	o	P _O = 50 mW
Beam divergence perpendicular to the junction	θ⊥	18	21	26	o	P _O = 50 mW
Astigmatism	As	—	5	—	μm	$P_0 = 5 \text{ mW}, \text{ NA} = 0.55$
Lasing wavelength	λp	655	658	662	nm	P ₀ = 50 mW

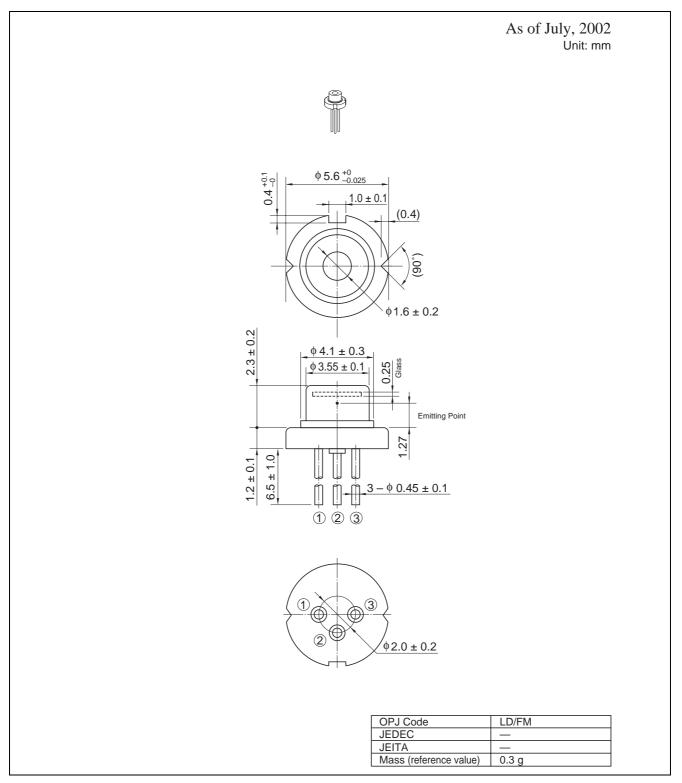


Typical Characteristic Curves





Package Dimensions





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- 2. This product contains gallium arsenide (GaAs), which may seriously endanger your health even at very low doses. Please avoid treatment which may create GaAs powder or gas, such as disassembly or performing chemical experiments, when you handle the product.

When disposing of the product, please follow the laws of your country and separate it from other waste such as industrial waste and household garbage.

3. Definition of items shown in this CAS is in accordance with that shown in Opto Device Databook issued by OPJ unless otherwise specified.

Sales Offices



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